## 2-Kb Microwire Serial CMOS EEPROM

# CAT93C57 Not Recommended for New Designs: Replace with CAT93C56

#### Description

The CAT93C56/57 is a 2–kb CMOS Serial EEPROM device which is organized as either 128 registers of 16 bits (ORG pin at  $V_{CC}$ ) or 256 registers of 8 bits (ORG pin at GND). Each register can be written (or read) serially by using the DI (or DO) pin. The CAT93C56/57 features sequential read and self–timed internal write with auto–clear. On–chip Power–On Reset circuitry protects the internal logic against powering up in the wrong state.

#### Features

- High Speed Operation: 2 MHz
- 1.8 V to 5.5 V Supply Voltage Range
- Selectable x8 or x16 Memory Organization
- Sequential Read
- Software Write Protection
- Power-up Inadvertent Write Protection
- Low Power CMOS Technology
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Industrial and Extended Temperature Ranges
- 8-pin PDIP, SOIC, TSSOP and 8-pad TDFN Packages
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

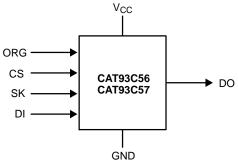


Figure 1. Functional Symbol

NOTE: When the ORG pin is connected to  $V_{CC}$ , the x16 organization is selected. When it is connected to ground, the x8 pin is selected. If the ORG pin is left unconnected, then an internal pullup device will select the x16 organization.



## **ON Semiconductor®**

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**X SUFFIX** 

CASE 751BE

V or W SUFFIX CASE 751BD

TDFN-8 VP2 SUFFIX CASE 511AK





PDIP-8 L SUFFIX CASE 646AA

TSSOP-8 Y SUFFIX CASE 948AL

#### PIN CONFIGURATIONS

CS	1	8	V <sub>CC</sub>	NC	1	8	ORG
SK	2	7	NC	V <sub>CC</sub>	2	7	GND
DI	3	6	ORG	CS	3	6	DO
DO	4	5	GND	SK	4	5	DI
			(V, X),	Ś	SOIC	(W*)	

TSSOP (Y), TDFN (VP2)

\* SOIC (W) rotated pin–out package not recommended for new designs

#### **PIN FUNCTION**

Pin Name	Function			
CS	Chip Select			
SK	Clock Input			
DI	Serial Data Input			
DO	Serial Data Output			
V <sub>CC</sub>	Power Supply			
GND	Ground			
ORG	Memory Organization			
NC	No Connection			

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 15 of this data sheet.

#### Table 1. ABSOLUTE MAXIMUM RATINGS

Parameters	Ratings	Units
Storage Temperature	-65 to +150	°C
Voltage on Any Pin with Respect to Ground (Note 1)	–0.5 to +6.5	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 The DC input voltage on any pin should not be lower than -0.5 V or higher than V<sub>CC</sub> + 0.5 V. During transitions, the voltage on any pin may undershoot to no less than -1.5 V or overshoot to no more than V<sub>CC</sub> + 1.5 V, for periods of less than 20 ns.

#### Table 2. RELIABILITY CHARACTERISTICS (Note 2)

Symbol	Parameter	Min	Units
N <sub>END</sub> (Note 3)	Endurance	1,000,000	Program / Erase Cycles
T <sub>DR</sub>	Data Retention	100	Years

2. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC–Q100 and JEDEC test methods.

3. Block Mode,  $V_{CC} = 5 V, 25^{\circ}C$ 

#### Table 3. D.C. OPERATING CHARACTERISTICS, CAT93C56

(V<sub>CC</sub> = +1.8 V to +5.5 V, T<sub>A</sub>=–40°C to +125°C unless otherwise specified.)

Symbol	Parameter	Test Cond	Min	Max	Units	
I <sub>CC1</sub>	Power Supply f <sub>SK</sub> = 1 MHz, V <sub>CC</sub> = 5.0 V Current (Write)				1	mA
I <sub>CC2</sub>	Power Supply Current (Read)	$f_{SK}$ = 1 MHz, $V_{CC}$ = 5.0 V			500	μΑ
I <sub>SB1</sub>	Power Supply	V <sub>IN</sub> = GND or V <sub>CC</sub> , CS = GND ORG = GND	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		2	μΑ
	Current (Standby) (x8 Mode)	CS = GND OKG = GND	$T_A = -40^{\circ}C$ to $+125^{\circ}C$		4	
I <sub>SB2</sub>	Power Supply Current (Standby)	$V_{IN} = GND \text{ or } V_{CC}, CS = GND ORG = Float or V_{CC}$	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1	μΑ
	(x16 Mode)	GIVD ONG = Float of V <sub>CC</sub>	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		2	
ILI	Input Leakage Current	kage $V_{IN} = GND$ to $V_{CC}$ $T_A = -40^{\circ}C$ to +85			1	μΑ
	Cunent		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		2	
I <sub>LO</sub> Output Leakage Current	V <sub>OUT</sub> = GND to V <sub>CC</sub> , CS = GND	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1	μΑ	
	Current	CS = GND	$T_A = -40^{\circ}C$ to $+125^{\circ}C$		2	
V <sub>IL1</sub>	Input Low Voltage	$4.5 \text{ V} \leq \text{V}_{\text{CC}} < 5.5 \text{ V}$		-0.1	0.8	V
V <sub>IH1</sub>	Input High Voltage	$4.5~\textrm{V} \leq \textrm{V}_{\textrm{CC}} < 5.5~\textrm{V}$		2	V <sub>CC</sub> + 1	V
$V_{\text{IL2}}$	Input Low Voltage	$1.8 \text{ V} \le \text{V}_{\text{CC}} < 4.5 \text{ V}$		0	V <sub>CC</sub> x 0.2	V
V <sub>IH2</sub>	Input High Voltage	$1.8 \text{ V} \le \text{V}_{\text{CC}} < 4.5 \text{ V}$		V <sub>CC</sub> x 0.7	V <sub>CC</sub> + 1	V
V <sub>OL1</sub>	Output Low Voltage	$4.5 \text{ V} \le \text{V}_{CC} < 5.5 \text{ V}, \ \text{I}_{OL} = 2.1 \text{ mA}$			0.4	V
V <sub>OH1</sub>	Output High Voltage	4.5 V $\leq$ V <sub>CC</sub> < 5.5 V, I <sub>OH</sub> = -400 $\mu$ A		2.4		V
V <sub>OL2</sub>	Output Low Voltage	$1.8 \text{ V} \le \text{V}_{CC} < 4.5 \text{ V}, \ \text{I}_{OL} = 1 \text{ mA}$			0.2	V
V <sub>OH2</sub>	Output High Voltage	$1.8 \text{ V} \le \text{V}_{CC} < 4.5 \text{ V}, \ \text{I}_{OH} = -100 \ \mu\text{A}$		V <sub>CC</sub> – 0.2		V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### Table 4. D.C. OPERATING CHARACTERISTICS, CAT93C57, Die Rev. E – Mature Product

(NOT RECOMMENDED FOR NEW DESIGNS) (V<sub>CC</sub> = +1.8 V to +5.5 V, T<sub>A</sub>=-40°C to +125°C unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Max	Units
I <sub>CC1</sub>	Power Supply Current (Write)	$f_{SK}$ = 1 MHz, $V_{CC}$ = 5.0 V		3	mA
I <sub>CC2</sub>	Power Supply Current (Read)	$f_{SK}$ = 1 MHz, $V_{CC}$ = 5.0 V		500	μΑ
I <sub>SB1</sub>	Power Supply Current (Standby) (x8 Mode)	V <sub>IN</sub> = GND or V <sub>CC</sub> , CS = GND ORG = GND		10	μΑ
I <sub>SB2</sub>	Power Supply Current (Standby) (x16 Mode)	$V_{IN} = GND \text{ or } V_{CC}, CS = GND$ ORG = Float or $V_{CC}$		10	μΑ
I <sub>LI</sub>	Input Leakage Current $V_{IN} = GND$ to $V_{CC}$			1	μΑ
I <sub>LO</sub>	Output Leakage Current	$V_{OUT}$ = GND to $V_{CC}$ , CS = GND		1	μΑ
V <sub>IL1</sub>	Input Low Voltage	$4.5 \text{ V} \le \text{ V}_{\text{CC}} < 5.5 \text{ V}$	-0.1	0.8	V
V <sub>IH1</sub>	Input High Voltage	$4.5 \text{ V} \le \text{V}_{\text{CC}} < 5.5 \text{ V}$	2	V <sub>CC</sub> + 1	V
V <sub>IL2</sub>	Input Low Voltage	$1.8 \text{ V} \leq \text{V}_{\text{CC}} < 4.5 \text{ V}$	0	V <sub>CC</sub> x 0.2	V
V <sub>IH2</sub>	Input High Voltage	$1.8 \text{ V} \le \text{ V}_{\text{CC}} < 4.5 \text{ V}$	V <sub>CC</sub> x 0.7	V <sub>CC</sub> + 1	V
V <sub>OL1</sub>	Output Low Voltage	4.5 V $\leq$ V <sub>CC</sub> < 5.5 V, I <sub>OL</sub> = 2.1 mA		0.4	V
V <sub>OH1</sub>	Output High Voltage	4.5 V $\leq$ V_{CC} < 5.5 V, I_{OH} = –400 $\mu\text{A}$	2.4		V
V <sub>OL2</sub>	Output Low Voltage	1.8 V $\leq$ V <sub>CC</sub> < 4.5 V, I <sub>OL</sub> = 1 mA		0.2	V
V <sub>OH2</sub>	Output High Voltage	$1.8 \text{ V} \le \text{V}_{CC}$ < 4.5 V, I <sub>OH</sub> = -100 $\mu$ A	V <sub>CC</sub> – 0.2		V

Table 5. PIN CAPACITANCE ( $T_A = 25^{\circ}C$ , f = 1 MHz,  $V_{CC} = 5$  V)

Symbol	Test	Conditions	Min	Тур	Max	Units
C <sub>OUT</sub> (Note 4)	Output Capacitance (DO)	V <sub>OUT</sub> = 0 V			5	pF
C <sub>IN</sub> (Note 4)	Input Capacitance (CS, SK, DI, ORG)	$V_{IN} = 0 V$			5	pF

4. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC–Q100 and JEDEC test methods.

#### Table 6. A.C. CHARACTERISTICS (Note 5), CAT93C56

(V<sub>CC</sub> = +1.8V to +5.5V,  $T_A = -40^{\circ}C$  to +125°C, unless otherwise specified.)

		Lim	Limits		
Symbol	Parameter	Min	Max	Units	
t <sub>CSS</sub>	CS Setup Time	50		ns	
t <sub>CSH</sub>	CS Hold Time	0		ns	
t <sub>DIS</sub>	DI Setup Time	100		ns	
t <sub>DIH</sub>	DI Hold Time	100		ns	
t <sub>PD1</sub>	Output Delay to 1		0.25	μs	
t <sub>PD0</sub>	Output Delay to 0		0.25	μs	
t <sub>HZ</sub> (Note 6)	Output Delay to High-Z		100	ns	
t <sub>EW</sub>	Program/Erase Pulse Width		5	ms	
t <sub>CSMIN</sub>	Minimum CS Low Time	0.25		μs	
t <sub>SKHI</sub>	Minimum SK High Time	0.25		μs	
t <sub>SKLOW</sub>	Minimum SK Low Time	0.25		μs	
t <sub>SV</sub>	Output Delay to Status Valid		0.25	μs	
SK <sub>MAX</sub>	Maximum Clock Frequency	DC	2000	kHz	

# Table 7. A.C. CHARACTERISTICS (Note 5), CAT93C57, Die Rev. E – Mature Product (NOT RECOMMENDED FOR NEW DESIGNS)

				Limi	ts			
			V <sub>CC</sub> = 1.8 V – 5.5 V		V <sub>CC</sub> = 2.5 V – 5.5 V		$V_{CC} = 4.5 V - 5.5 V$	
Symbol	Parameter	Min	Max	Min	Мах	Min	Max	Units
t <sub>CSS</sub>	CS Setup Time	200		100		50		ns
t <sub>CSH</sub>	CS Hold Time	0		0		0		ns
t <sub>DIS</sub>	DI Setup Time	400		200		100		ns
t <sub>DIH</sub>	DI Hold Time	400		200		100		ns
t <sub>PD1</sub>	Output Delay to 1		1		0.5		0.25	μS
t <sub>PD0</sub>	Output Delay to 0		1		0.5		0.25	μS
t <sub>HZ</sub> (Note 6)	Output Delay to High–Z		400		200		100	ns
t <sub>EW</sub>	Program/Erase Pulse Width		10		10		10	ms
t <sub>CSMIN</sub>	Minimum CS Low Time	1		0.5		0.25		μs
t <sub>SKHI</sub>	Minimum SK High Time	1		0.5		0.25		μS
t <sub>SKLOW</sub>	Minimum SK Low Time	1		0.5		0.25		μS
t <sub>SV</sub>	Output Delay to Status Valid		1		0.5		0.25	μS
SK <sub>MAX</sub>	Maximum Clock Frequency	DC	250	DC	500	DC	1000	kHz

#### Table 8. POWER-UP TIMING (Notes 6 and 7)

Symbol	Parameter	Max	Units
t <sub>PUR</sub>	Power-up to Read Operation	1	ms
t <sub>PUW</sub>	Power-up to Write Operation	1	ms

5. Test conditions according to "A.C. Test Conditions" table.

6. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate

AEC-Q100 and JEDEC test methods.

7.  $t_{PUR}$  and  $t_{PUW}$  are the delays required from the time  $V_{CC}$  is stable until the specified operation can be initiated.

#### Table 9. A.C. TEST CONDITIONS

Input Rise and Fall Times	≤ 50 ns		
Input Pulse Voltages	0.4 V to 2.4 V	$4.5 \text{ V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{ V}$	
Timing Reference Voltages	0.8 V, 2.0 V	$4.5 \text{ V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{ V}$	
Input Pulse Voltages	0.2 $V_{CC}$ to 0.7 $V_{CC}$	$1.8 \text{ V} \leq \text{V}_{\text{CC}} \leq 4.5 \text{ V}$	
Timing Reference Voltages	0.5 V <sub>CC</sub>	$1.8 \text{ V} \leq \text{V}_{\text{CC}} \leq 4.5 \text{ V}$	
Output Load	Current Source I <sub>OLmax</sub> /I <sub>OHmax</sub> ; CL=100 pF		

#### **Device Operation**

The CAT93C56/57 is a 2048–bit nonvolatile memory intended for use with industry standard microprocessors. The CAT93C56/57 can be organized as either registers of 16 bits or 8 bits. When organized as X16, seven 10–bit instructions for 93C57 or seven 11–bit instructions for 93C56 control the reading, writing and erase operations of the device. When organized as X8, seven 11–bit instructions for 93C57 or seven 12–bit instructions for 93C56 control the reading, writing and erase operations of the device. The CAT93C56/57 operates on a single power supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data

from the device, or when checking the ready/busy status after a write operation. The serial communication protocol follows the timing shown in Figure 2.

The ready/busy status can be determined after the start of internal write cycle by selecting the device (CS high) and polling the DO pin; DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. If necessary, the DO pin may be placed back into a high impedance state during chip select by shifting a dummy "1" into the DI pin. The DO pin will enter the high impedance state on the rising edge of the clock (SK). Placing the DO pin into the high impedance state is recommended in applications where the DI pin and the DO pin are to be tied together to form a common DI/O pin.

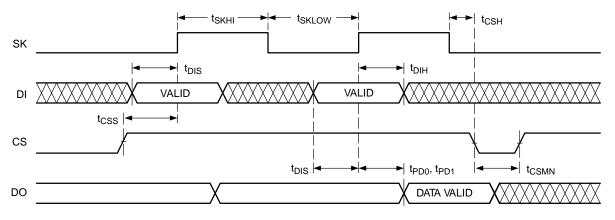


Figure 2. Synchronous Data Timing

The format for all instructions sent to the device is a logical "1" start bit, a 2-bit (or 4-bit) opcode, 7-bit address (CAT93C57) / 8-bit address (CAT93C56) (an additional bit

when organized X8) and for write operations a 16–bit data field (8–bit for X8 organizations). The instruction format is shown in Instruction Set table.

		Start		Add	ress	Data		
Instruction	Device Type	Bit	Opcode	x8	x16	x8	x16	Comments
READ	93C56 (Note 8)	1	10	A8–A0	A7–A0			Read Address
	93C57	1	10	A7–A0	A6-A0			AN–A0
ERASE	93C56 (Note 8)	1	11	A8–A0	A7–A0			Clear Address
	93C57	1	11	A7–A0	A6-A0			AN–A0
WRITE	93C56 (Note 8)	1	01	A8–A0	A7–A0	D7-D0	D15–D0	Write Address
	93C57	1	01	A7-A0	A6-A0	D7-D0	D15–D0	AN–A0
EWEN	93C56 (Note 8)	1	00	11XXXXXXX	11XXXXXX			Write Enable
	93C57	1	00	11XXXXXX	11XXXXX			
EWDS	93C56 (Note 8)	1	00	00XXXXXXX	00XXXXXX			Write Disable
	93C57	1	00	00XXXXXX	00XXXXX			
ERAL	93C56 (Note 8)	1	00	10XXXXXXX	10XXXXXX			Clear All
	93C57	1	00	10XXXXXX	10XXXXX			Addresses
WRAL	93C56 (Note 8)	1	00	01XXXXXXX	01XXXXXX	D7-D0	D15–D0	Write All
	93C57	1	00	01XXXXXX	01XXXXX	D7-D0	D15–D0	Addresses

#### Table 10. INSTRUCTION SET

8. Address bit A8 for 256x8 organization and A7 for 128x16 organization are "Don't Care" bits, but must be kept at either a "1" or "0" for READ, WRITE and ERASE commands.

#### Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the CAT93C56/57 will come out of the high impedance state and, after sending an initial dummy zero bit, will begin shifting out the data addressed (MSB first). The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay ( $t_{PD0}$  or  $t_{PD1}$ ).

For the CAT93C56/57, after the initial data word has been shifted out and CS remains asserted with the SK clock continuing to toggle, the device will automatically increment to the next address and shift out the next data word in a sequential READ mode. As long as CS is continuously asserted and SK continues to toggle, the device will keep incrementing to the next address automatically until it reaches to the end of the address space, then loops back to address 0. In the sequential READ mode, only the initial data word is preceded by a dummy zero bit. All subsequent data words will follow without a dummy zero bit. The READ instruction timing is illustrated in Figure 3.

#### Erase/Write Enable and Disable

The CAT93C56/57 powers up in the write disable state. Any writing after power–up or after an EWDS (erase/write disable) instruction must first be preceded by the EWEN (erase/write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all CAT93C56/57 write and erase instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/disable status. The EWEN and EWDS instructions timing is shown in Figure 4.

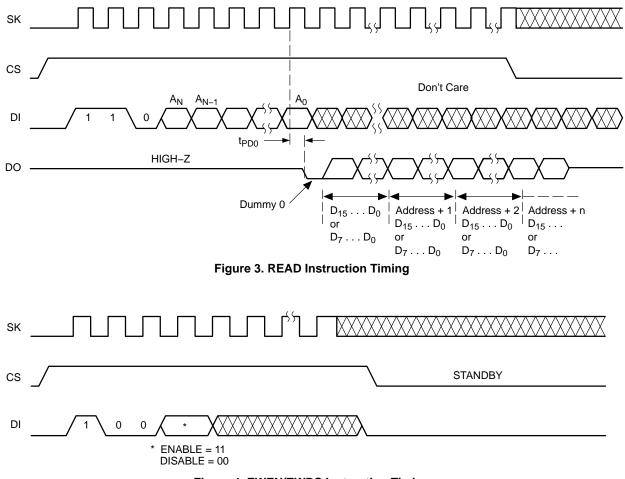


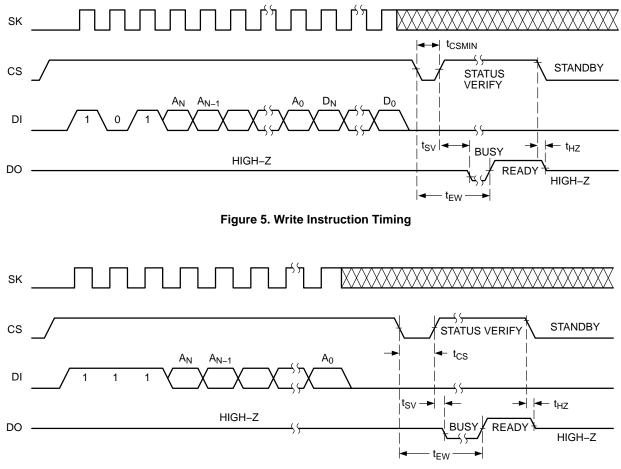
Figure 4. EWEN/EWDS Instruction Timing

#### Write

After receiving a WRITE command (Figure 5), address and the data, the CS (Chip Select) pin must be deselected for a minimum of  $t_{CSMIN}$ . The falling edge of CS will start the self clocking clear and data store cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C56/57 can be determined by selecting the device and polling the DO pin. Since this device features Auto–Clear before write, it is NOT necessary to erase a memory location before it is written into.

#### Erase

Upon receiving an ERASE command and address, the CS (Chip Select) pin must be deasserted for a minimum of  $t_{CSMIN}$  (Figure 6). The falling edge of CS will start the self clocking clear cycle of the selected memory location. The clocking of the SaK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C56/57 can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical "1" state.





#### Erase All

Upon receiving an ERAL command (Figure 7), the CS (Chip Select) pin must be deselected for a minimum of  $t_{CSMIN}$ . The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C56/57 can be determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits return to a logical "1" state.

#### Write All

Upon receiving a WRAL command and data, the CS (Chip Select) pin must be deselected for a minimum of  $t_{CSMIN}$  (Figure 8). The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C56/57 can be determined by selecting the device and polling the DO pin. It is not necessary for all memory locations to be cleared before the WRAL command is executed.

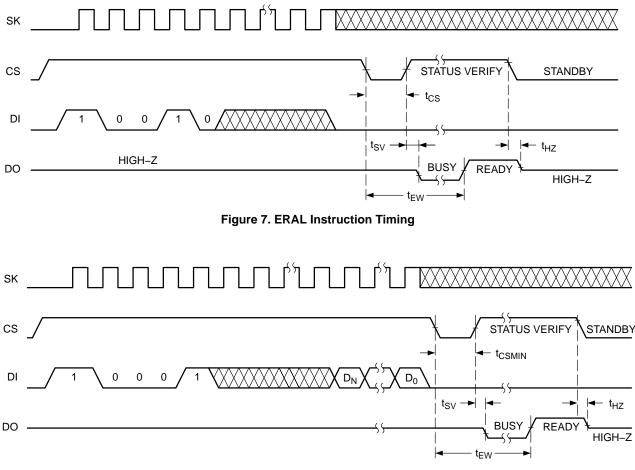
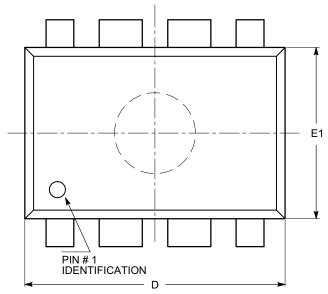


Figure 8. WRAL Instruction Timing

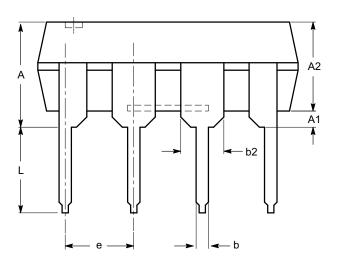
#### PACKAGE DIMENSIONS

PDIP-8, 300 mils CASE 646AA-01 ISSUE A



SYMBOL	MIN NOM		МАХ
А			5.33
A1	0.38		
A2	2.92	3.30	4.95
b	0.36	0.46	0.56
b2	1.14	1.52	1.78
с	0.20	0.25	0.36
D	9.02	9.27	10.16
E	7.62	7.87	8.25
E1	6.10	6.35	7.11
е	2.54 BSC		
eB	7.87		10.92
L	2.92	3.30	3.80

TOP VIEW

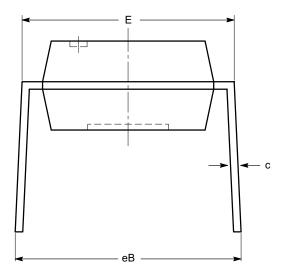


SIDE VIEW

#### Notes:

(1) All dimensions are in millimeters.

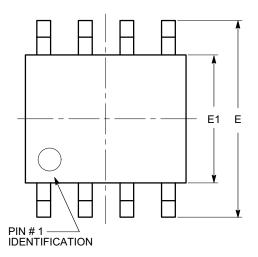
(2) Complies with JEDEC MS-001.



END VIEW

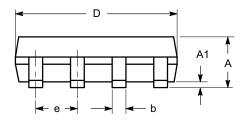
#### PACKAGE DIMENSIONS

SOIC 8, 150 mils CASE 751BD-01 ISSUE O



SYMBOL	MIN	NOM	MAX
А	1.35		1.75
A1	0.10		0.25
b	0.33		0.51
с	0.19		0.25
D	4.80		5.00
Е	5.80		6.20
E1	3.80		4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
θ	0°		8°

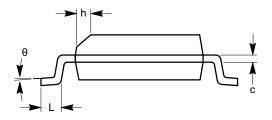
TOP VIEW



SIDE VIEW

#### Notes:

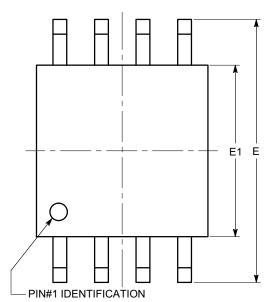
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MS-012.





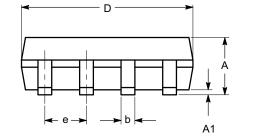
#### PACKAGE DIMENSIONS

**SOIC-8, 208 mils** CASE 751BE-01 ISSUE O

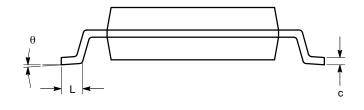


SYMBOL	MIN	NOM	MAX
A			2.03
A1	0.05		0.25
b	0.36		0.48
с	0.19		0.25
D	5.13		5.33
E	7.75		8.26
E1	5.13		5.38
е		1.27 BSC	
L	0.51		0.76
θ	0°		8°

TOP VIEW



SIDE VIEW



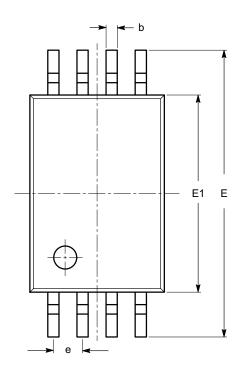
END VIEW

#### Notes:

All dimensions are in millimeters. Angles in degrees.
Complies with EIAJ EDR-7320.

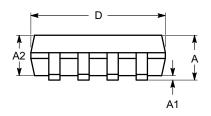
#### PACKAGE DIMENSIONS

TSSOP8, 4.4x3 CASE 948AL-01 ISSUE O

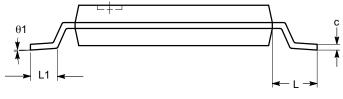


SYMBOL	MIN	NOM	MAX
А			1.20
A1	0.05		0.15
A2	0.80	0.90	1.05
b	0.19		0.30
С	0.09		0.20
D	2.90	3.00	3.10
E	6.30	6.40	6.50
E1	4.30	4.40	4.50
е	0.65 BSC		
L	1.00 REF		
L1	0.50	0.60	0.75
θ	0°		8°

#### TOP VIEW



SIDE VIEW



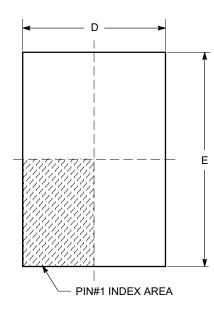
END VIEW

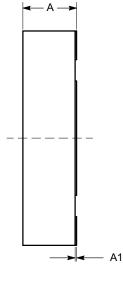
#### Notes:

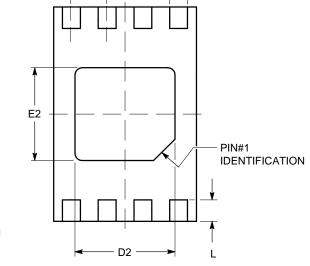
All dimensions are in millimeters. Angles in degrees.
Complies with JEDEC MO-153.

#### PACKAGE DIMENSIONS

**TDFN8**, 2x3 CASE 511AK-01 ISSUE A







b -

е

TOP VIEW

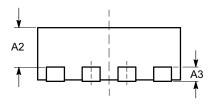
SIDE VIEW

SYMBOL	MIN NOM		MAX	
А	0.70	0.75	0.80	
A1	0.00	0.02	0.05	
A2	0.45 0.55 0.0			
A3	0.20 REF			
b	0.20	0.25	0.30	
D	1.90	2.00	2.10	
D2	1.30	1.40	1.50	
Е	2.90	3.00	3.10	
E2	1.20	1.30	1.40	
e	0.50 TYP			
L	0.20	0.30	0.40	

#### Notes:

All dimensions are in millimeters.
Complies with JEDEC MO-229.

**BOTTOM VIEW** 



FRONT VIEW

#### **Example of Ordering Information**

OPN	Specific Device Marking	Pkg Type	Temperature Range	Lead Fin- ish	Shipping
CAT93C56LI-G	CSI*4G / 93C56LI	PDIP-8	l = Industrial (-40°C to +85°C)	NiPdAu	Tube, 50 Units / Tube
CAT93C56VE-G	CSI*4G / 93C56LE	SOIC-8, JEDEC	E = Extended (-40°C to +125°C)	NiPdAu	Tube, 100 Units / Tube
CAT93C56VE-GT3	CSI*4G / 93C56VE	SOIC-8, JEDEC	E = Extended (-40°C to +125°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C56VI–G	CSI*4G / 93C56VI	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tube, 100 Units / Tube
CAT93C56VI-GT3	CSI*4G / 93C56VI	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C56VP2I-GT3	HB	TDFN-8	l = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C56WI-G	CSI*4G / 93C56WI	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tube, 100 Units / Tube
CAT93C56WI-GT3	93C56W	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C56XI	CSI*3G / 93C56XI	SOIC-8, EIAJ	l = Industrial (-40°C to +85°C)	Matte-Tin	Tube, 94 Units / Tube
CAT93C56XI-T2	CSI*3G / 93C56XI	SOIC-8, EIAJ	l = Industrial (-40°C to +85°C)	Matte-Tin	Tape & Reel, 2000 Units / Reel
CAT93C56YI–G	M56	TSSOP-8	l = Industrial (-40°C to +85°C)	NiPdAu	Tube, 100 Units / Tube
CAT93C56YI-GT3	M56	TSSOP-8	l = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C57LI–G	CSI*4E/ 93C57LI	PDIP-8	I = Industrial (-40°C to +85°C)	NiPdAu	Tube, 50 Units / Tube
CAT93C57VI–G	CSI*4E / 93C57VI	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tube, 100 Units / Tube
CAT93C57VI-GT3	CSI*4E / 93C57VI	SOIC-8, JEDEC	l = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel
CAT93C57XI	CSI*3E / 93C57X	SOIC-8, EIAJ	l = Industrial (-40°C to +85°C)	Matte-Tin	Tube, 94 Units / Tube
CAT93C57XI-T2	CSI*3E / 93C57X	SOIC-8, EIAJ	l = Industrial (-40°C to +85°C)	Matte-Tin	Tape & Reel, 2000 Units / Reel
CAT93C57YI–GT3	M57	TSSOP-8	I = Industrial (-40°C to +85°C)	NiPdAu	Tape & Reel, 3000 Units / Reel

9. All packages are RoHS-compliant (Lead-free, Halogen-free).
10. The standard lead finish is NiPdAu.
11. CAT93C57 NOT recommended for new designs.
12. For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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